FlipKY®
Chip Scale Package Schottky Barrier Rectifier, 0.5 A

FlipKY®

FEATURES

- Ultra low V_F to footprint area
- Very low profile (< 0.6 mm)
- Low thermal resistance
- Supplied tested and on tape and reel

Pb-free
RoHS COMPLIANT

APPLICATIONS

- Reverse polarity protection
- Current steering
- Freewheeling
- Flyback
- Oring

DESCRIPTION

Vishay's FlipKY® product family utilizes wafer level chip scale packaging to deliver Schottky diodes with the lowest V_F to PCB footprint area in industry. The three pad 0.9 mm x 1.2 mm devices can deliver up to 0.5 A and occupy only 1.08 mm^2 of board space. The anode and cathode connections are made through solder bump pads on one side of the silicon enabling designers to strategically place the diodes on the PCB. This design not only minimizes board space but also reduces thermal resistance and inductance, which can improve overall circuit efficiency.

Typical applications include hand-held, portable equipment such as cell phones, MP3 players, bluetooth, GPS, PDAs, and portable hard disk drives where space savings and performance are crucial.

PRODUCT SUMMARY	
$I_{F(AV)}$	0.5 A
V_R	40 V

MAJOR RATINGS AND CHARACTERISTICS			
SYMBOL	CHARACTERISTICS	MAX.	UNITS
V_{RRM}		40	V
$I_{F(AV)}$	Rectangular waveform	0.5	A
I_{FSM}		190	
V_F	0.5 Apk, T_J = 125 °C	0.42	V
T_J		- 55 to 150	°C

VOLTAGE RATINGS			
PARAMETER	SYMBOL	FCSP05H40TR	UNITS
Maximum DC reverse voltage	V_R	40	V
Maximum working peak reverse voltage	V_{RWM}		

FCSP05H40TR

Vishay High Power Products

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ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	TEST CONDITIONS		VALUES	UNITS
Maximum average forward current	$I_{F(AV)}$	50 % duty cycle at T_{PCB} = 114 °C, rectangular waveform		0.5	A
Maximum peak one cycle non-repetitive surge current at 25 °C	I_{FSM}	5 µs sine or 3 µs rect. pulse	Following any rated load condition and with rated V_{RRM} applied	190	
		10 ms sine or 6 ms rect. pulse		10	
Non-repetitive avalanche energy	E_{AS}	T_J = 25 °C, I_{AS} = 2.0 A, L = 5.0 mH		5	mJ
Repetitive avalanche current	I_{AR}	Current decaying linearly to zero in 1 µs Frequency limited by T_J maximum V_A = 1.5 x V_R typical		0.5	A

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		TYP.	MAX.	UNITS
Maximum forward voltage drop See fig. 1	V_{FM} (1)	0.5 A	T_J = 25 °C	0.48	0.52	V
		1 A		0.54	0.58	
		0.5 A	T_J = 125 °C	0.38	0.42	
		1 A		0.46	0.50	
Maximum reverse leakage current See fig. 2	I_{RM} (1)	T_J = 25 °C	V_R = Rated V_R	1	10	µA
			V_R = 20 V	0.2	0.5	
			V_R = 10 V	0.08	0.25	
			V_R = 5 V	0.05	0.15	
		T_J = 125 °C	V_R = Rated V_R	0.5	2	mA
			V_R = 20 V	0.2	1	
			V_R = 10 V	0.15	0.8	
			V_R = 5 V	0.125	0.5	
Maximum junction capacitance	C_T	V_R = 5 V_{DC} (test signal range 100 kHz to 1 MHz) 25 °C		-	90	pF
Maximum voltage rate of charge	dV/dt	Rated V_R		-	10 000	V/µs

Note

(1) Pulse width < 300 µs, duty cycle < 2 %

THERMAL - MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum junction and storage temperature range	T_J (1), T_{Stg}		- 55 to 150	°C
Typical thermal resistance, junction to PCB	R_{thJL} (2)	DC operation	35	°C/W
Maximum thermal resistance, junction to ambient	R_{thJA}		150	

Notes

(1) $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{thJA}}$ thermal runaway condition for a diode on its own heatsink

(2) Mounted on minimum footprint PCB

For technical questions, contact: diodes-tech@vishay.com

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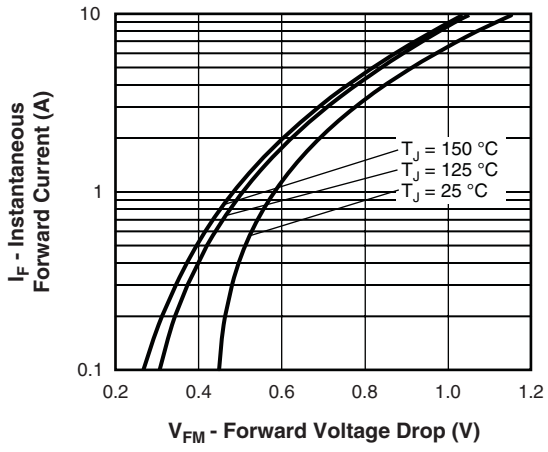

Fig. 1 - Maximum Forward Voltage Drop Characteristics (Per Leg)

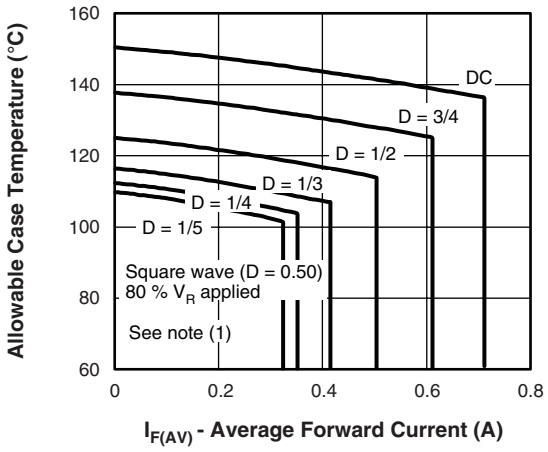

Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current (Per Leg)

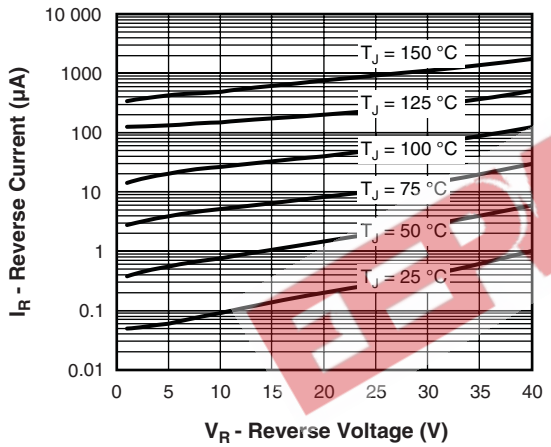

Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage (Per Leg)

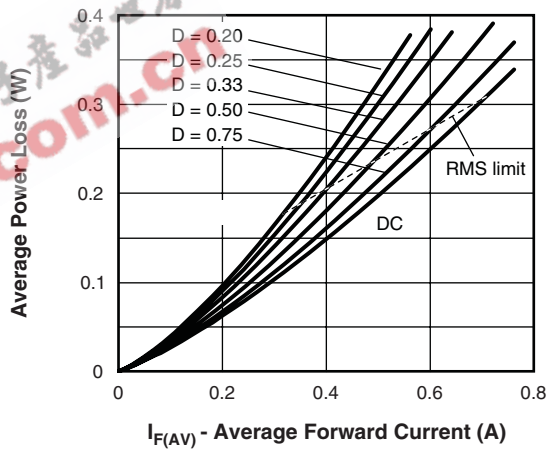

Fig. 5 - Forward Power Loss Characteristics (Per Leg)

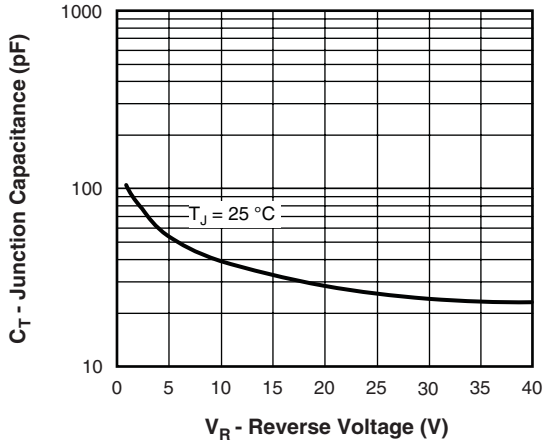

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Leg)

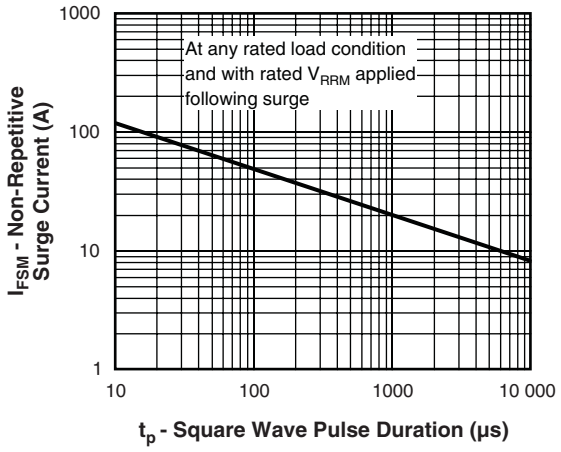

Fig. 6 - Maximum Non-Repetitive Surge Current (Per Leg)

Note

(1) Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;
Pd = Forward power loss = $I_{F(AV)} \times V_{FM}$ at ($I_{F(AV)}$/D) (see fig. 6); Pd_{REV} = Inverse power loss = $V_{R1} \times I_R$ (1 - D); I_R at 80 % V_R applied

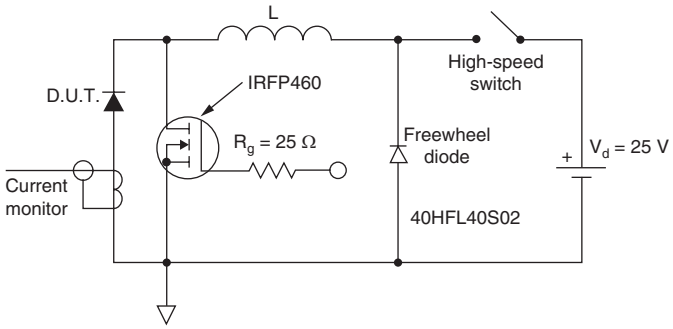

Fig. 7 - Unclamped Inductive Test Circuit

LINKS TO RELATED DOCUMENTS	
Dimensions	http://www.vishay.com/doc?95049
Part marking information	http://www.vishay.com/doc?95060
Packaging information	http://www.vishay.com/doc?95062

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